



浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

产品规格书

Specification of products

产品名称：可控硅模块

产品型号：MFC110A3500VY01

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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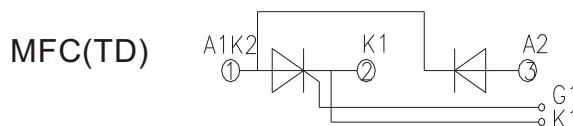
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拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c=85^\circ C$	125			110	A
$I_{T(RMS)}$	RMS on-state current					173	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}$ tp=10ms $V_{DSM} \& V_{RSM} = V_{DRM} \& V_{RRM} + 200V$ respectively	125		3500		V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			15	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=60\%V_{RRM}$	125			2.1	kA
I^2t	I^2t for fusing coordination					22	$A^2s * 10^3$
V_{TO}	Threshold voltage		125			1.15	V
r_T	On-state slope resistance					2.88	$m\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=330A$	25			2.20	V
V_{FM}	Peak on-state voltage	$I_{FM}=330A$	25			1.20	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			800	$V/\mu s$
di/dt	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu s$ Repetitive	125			100	$A/\mu s$
I_{GT}	Gate trigger current	$V_A=12V, I_A=1A$	25	30		150	mA
V_{GT}	Gate trigger voltage			0.8		2.5	V
I_H	Holding current			10		200	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.2			V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.19	$^\circ C/W$
$R_{th(c-h)}$	Thermal resistance case to heat sink	Single side cooled per chip				0.15	$^\circ C/W$
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min, $I_{iso}:1mA(MAX)$		4000			V
F_m	Terminal connection torque (M6)				5.0		$N\cdot m$
	Mounting torque (M6)				5.0		$N\cdot m$
T_{vj}	Junction temperature			-40		125	$^\circ C$
T_{stg}	Stored temperature			-40		125	$^\circ C$
W_t	Weight				370		g
Outline							

OUTLINE DRAWING & CIRCUIT DIAGRAM



Rating and Characteristic

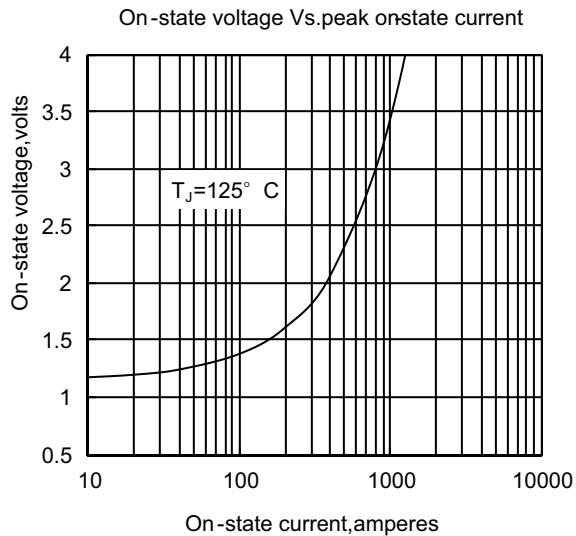


Fig. 1

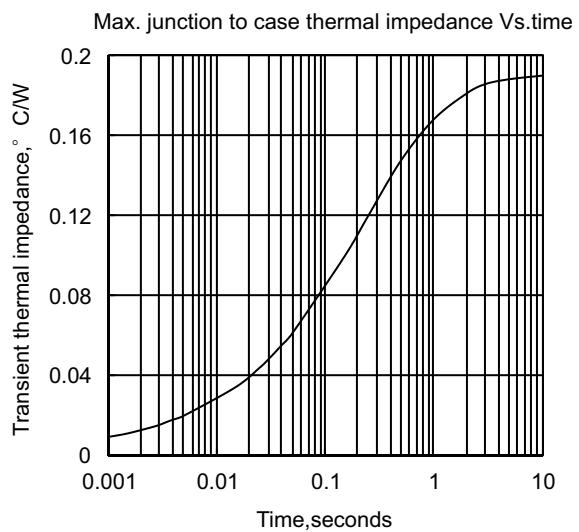


Fig. 2

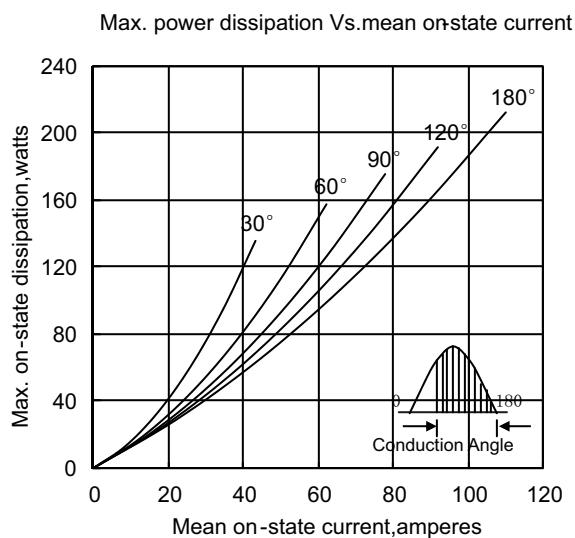


Fig. 3

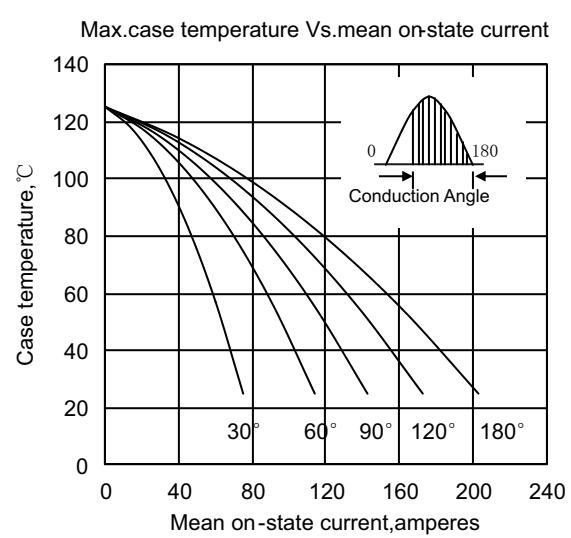


Fig. 4

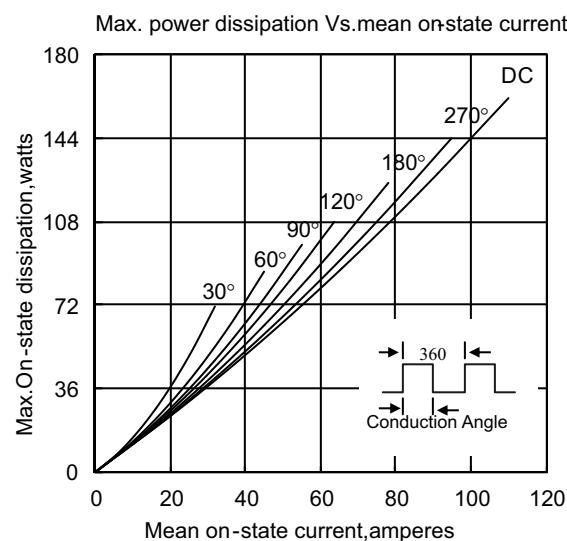


Fig. 5

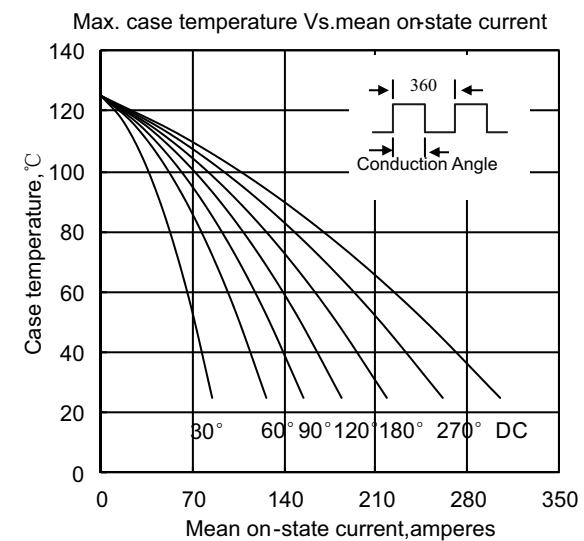


Fig. 6

Rating and Characteristic

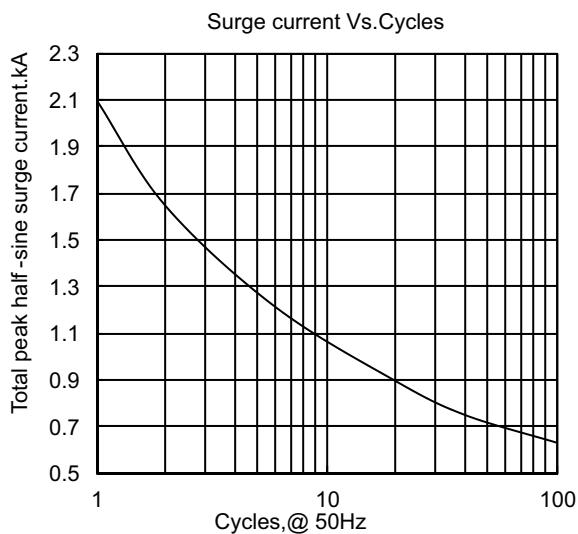


Fig. 7

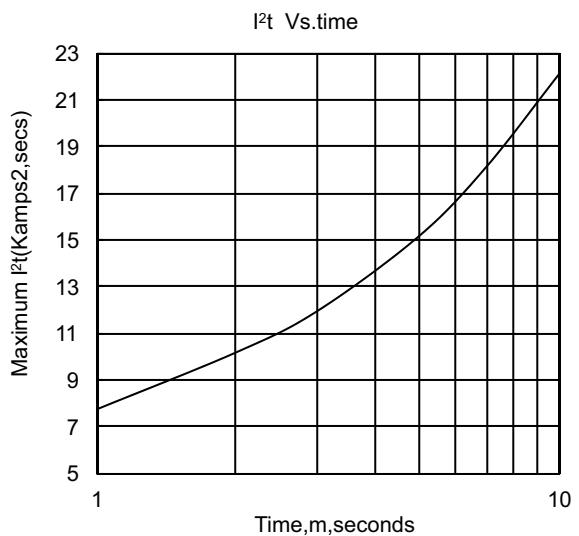


Fig. 8

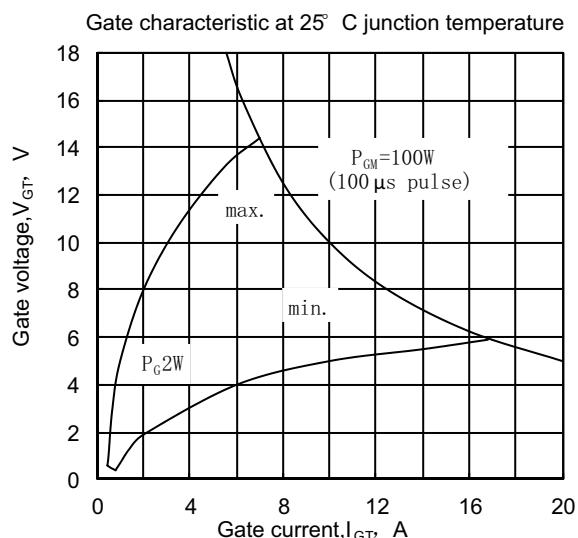


Fig. 9

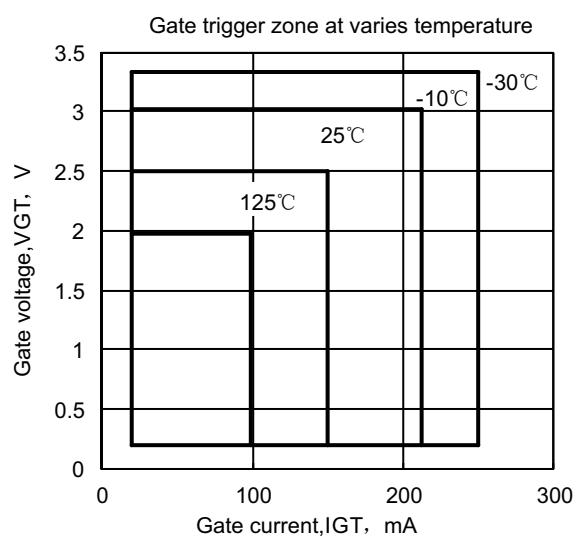


Fig. 10

Outside Dimension

